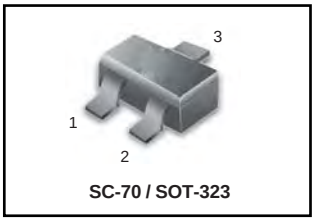
JXND ELECTRONICS CO.,LTD

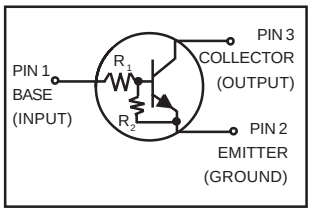
Bias Resistor Transistor NPN Silicon
MUN5211T1G Series
S-MUN5211T1G Series

This new series of digital transistors is designed to replace a single device and its external resistor bias network. The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space. The device is housed in the SC–70/SOT–323 package which is designed for low power surface mount applications.

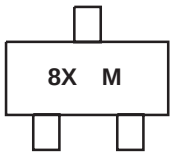
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- The SC–70/SOT–323 package can be soldered using wave or reflow. The modified gull–winged leads absorb thermal stress during soldering eliminating the possibility of damage to the die.
- Available in 8 mm embossed tape and reel
  Use the Device Number to order the 7 inch/3000 unit reel.
- Pb-Free package is available
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SC-70 / SOT-323



MARKING DIAGRAM



8x = Specific Device Code
x = (See Marking Table)
M= Date Code

DEVICE MARKING INFORMATION

See specific marking information in the device marking table on page 2 of this data sheet.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C Derate above 25°C	P_D	202 (Note 1.) 310 (Note 2.) 1.6 (Note 1.) 2.5 (Note 2.)	mW mW/°C
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	618 (Note 1.) 403 (Note 2.)	°C/W
Thermal Resistance – Junction-to-Lead	$R_{\theta JL}$	280 (Note 1.) 332 (Note 2.)	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	–55 to +150	°C

1. FR–4 @ Minimum Pad
2. FR–4 @ 1.0 x 1.0 inch Pad

Bias Resistor Transistor NPN Silicon
MUN5211T1G Series
S-MUN5211T1G Series

DEVICE MARKING RESISTOR VALUES AND ORDERING INFORMATION

Device	Package	Marking	R1(K)	R2(K)	Shipping
MUN5211T1G	SC-70/SOT-323	8A	10	10	3000/Tape&Reel
MUN5211T3G	SC-70/SOT-323	8A	10	10	10000/Tape&Reel
MUN5212T1G	SC-70/SOT-323	8B	22	22	3000/Tape&Reel
MUN5212T3G	SC-70/SOT-323	8B	22	22	10000/Tape&Reel
MUN5213T1G	SC-70/SOT-323	8C	47	47	3000/Tape&Reel
MUN5213T3G	SC-70/SOT-323	8C	47	47	10000/Tape&Reel
MUN5214T1G	SC-70/SOT-323	8D	10	47	3000/Tape&Reel
MUN5214T3G	SC-70/SOT-323	8D	10	47	10000/Tape&Reel
MUN5215T1G(Note 3)	SC-70/SOT-323	8E	10	∞	3000/Tape&Reel
MUN5215T3G	SC-70/SOT-323	8E	10	∞	10000/Tape&Reel
MUN5216T1G(Note 3)	SC-70/SOT-323	8F	4.7	∞	3000/Tape&Reel
MUN5216T3G	SC-70/SOT-323	8F	4.7	∞	10000/Tape&Reel
MUN5230T1G(Note 3)	SC-70/SOT-323	8G	1	1	3000/Tape&Reel
MUN5230T3G	SC-70/SOT-323	8G	1	1	10000/Tape&Reel
MUN5231T1G(Note 3)	SC-70/SOT-323	8H	2.2	2.2	3000/Tape&Reel
MUN5231T3G	SC-70/SOT-323	8H	2.2	2.2	10000/Tape&Reel
MUN5232T1G(Note 3)	SC-70/SOT-323	8J	4.7	4.7	3000/Tape&Reel
MUN5232T3G	SC-70/SOT-323	8J	4.7	4.7	10000/Tape&Reel
MUN5233T1G(Note 3)	SC-70/SOT-323	8K	4.7	47	3000/Tape&Reel
MUN5233T3G	SC-70/SOT-323	8K	4.7	47	10000/Tape&Reel
MUN5234T1G(Note 3)	SC-70/SOT-323	8L	22	47	3000/Tape&Reel
MUN5234T3G	SC-70/SOT-323	8L	22	47	10000/Tape&Reel
MUN5235T1G(Note 3)	SC-70/SOT-323	8M	2.2	47	3000/Tape&Reel
MUN5235T3G	SC-70/SOT-323	8M	2.2	47	10000/Tape&Reel
MUN5236T1G(Note 3)	SC-70/SOT-323	8N	100	100	3000/Tape&Reel
MUN5236T3G	SC-70/SOT-323	8N	100	100	10000/Tape&Reel
MUN5237T1G(Note 3)	SC-70/SOT-323	8P	47	22	3000/Tape&Reel
MUN5237T3G	SC-70/SOT-323	8P	47	22	10000/Tape&Reel

3. New devices. Updated curves to follow in subsequent data sheets.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)		I_{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V_{CE} = 50 V, I_B = 0)		I_{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0 V, I_C = 0)	MUN5211T1G	I_{EBO}	–	–	0.5	mAdc
	MUN5212T1G		–	–	0.2	
	MUN5213T1G		–	–	0.1	
	MUN5214T1G		–	–	0.2	
	MUN5215T1G		–	–	0.9	
	MUN5216T1G		–	–	1.9	
	MUN5230T1G		–	–	4.3	
	MUN5231T1G		–	–	2.3	
	MUN5232T1G		–	–	1.5	
	MUN5233T1G		–	–	0.18	
	MUN5234T1G		–	–	0.13	
	MUN5235T1G		–	–	0.2	
	MUN5236T1G		–	–	0.05	
	MUN5237T1G		–	–	0.13	
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)		$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 4.) (I_C = 2.0 mA, I_B = 0)		$V_{(BR)CEO}$	50	–	–	Vdc
ON CHARACTERISTICS (Note 4.)						
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	MUN5211T1G	h_{FE}	35	60	220	
	MUN5212T1G		60	100	–	
	MUN5213T1G		80	140	320	
	MUN5214T1G		80	140	–	
	MUN5215T1G		160	350	–	
	MUN5216T1G		160	350	–	
	MUN5230T1G		3.0	5.0	–	
	MUN5231T1G		8.0	15	–	
	MUN5232T1G		15	30	–	
	MUN5233T1G		80	200	–	
	MUN5234T1G		80	150	–	
	MUN5235T1G		80	140	–	
	MUN5236T1G		80	150	–	
	MUN5237T1G		80	140	–	
Collector-Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA) (I_C = 10 mA, I_B = 5 mA) LMUN5230T1/LMUN5231T1 (I_C = 10 mA, I_B = 1 mA) LMUN5215T1/LMUN5216T1/ LMUN5232T1/LMUN5233T1/LMUN5234T1		$V_{CE(sat)}$	–	–	0.25	Vdc
Output Voltage (on)		V_{OL}				Vdc
(V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)	MUN5211T1G		–	–	0.2	
	MUN5212T1G		–	–	0.2	
	MUN5214T1G		–	–	0.2	
	MUN5215T1G		–	–	0.2	
	MUN5216T1G		–	–	0.2	
	MUN5230T1G		–	–	0.2	
	MUN5231T1G		–	–	0.2	
	MUN5232T1G		–	–	0.2	
	MUN5233T1G		–	–	0.2	
	MUN5234T1G		–	–	0.2	
	MUN5235T1G		–	–	0.2	
(V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 kΩ)	MUN5213T1G		–	–	0.2	
(V_{CC} = 5.0 V, V_B = 5.5 V, R_L = 1.0 kΩ)	MUN5236T1G		–	–	0.2	
(V_{CC} = 5.0 V, V_B = 4.0 V, R_L = 1.0 kΩ)	MUN5237T1G		–	–	0.2	

4. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 5.) (Continued)						
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ) (V_{CC} = 5.0 V, V_B = 0.050 V, R_L = 1.0 kΩ) (V_{CC} = 5.0 V, V_B = 0.25 V, R_L = 1.0 kΩ)	MUN5230T1G MUN5215T1G MUN5216T1G MUN5233T1G	V_{OH}	4.9	–	–	Vdc
Input Resistor	MUN5211T1G	R_1	7.0	10	13	kΩ
	MUN5212T1G		15.4	22	28.6	
	MUN5213T1G		32.9	47	61.1	
	MUN5214T1G		7.0	10	13	
	MUN5215T1G		7.0	10	13	
	MUN5216T1G		3.3	4.7	6.1	
	MUN5230T1G		0.7	1.0	1.3	
	MUN5231T1G		1.5	2.2	2.9	
	MUN5232T1G		3.3	4.7	6.1	
	MUN5233T1G		3.3	4.7	6.1	
	MUN5234T1G		15.4	22	28.6	
	MUN5235T1G		1.54	2.2	2.86	
	MUN5236T1G		70	100	130	
	MUN5237T1G		32.9	47	61.1	
Resistor Rati	MUN5211T1G/MUN5212T1G/MUN5213T1G/ MUN5236T1G	R_1/R_2	0.8	1.0	1.2	
	MUN5214T1G		0.17	0.21	0.25	
	MUN5215T1G/MUN5216T1G		–	–	–	
	MUN5230T1G/MUN5231T1G/MUN5232T1G		0.8	1.0	1.2	
	MUN5233T1G		0.055	0.1	0.185	
	MUN5234T1G		0.38	0.47	0.56	
	MUN5235T1G		0.038	0.047	0.056	
	MUN5237T1G		1.7	2.1	2.6	

5. Pulse Test: Pulse Width < 300 μs, Duty Cycle < 2.0%

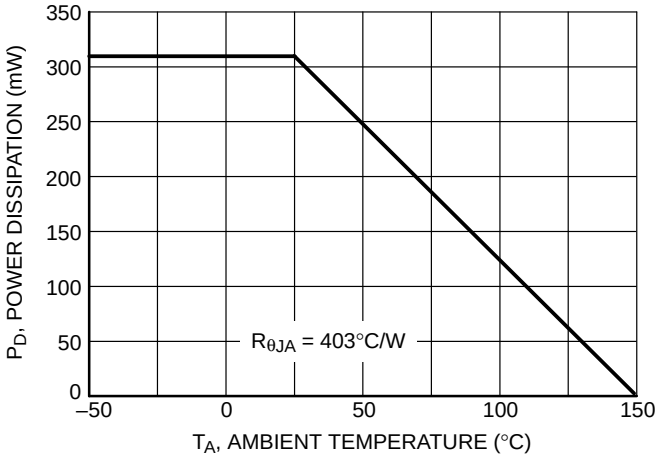


Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5211T1G

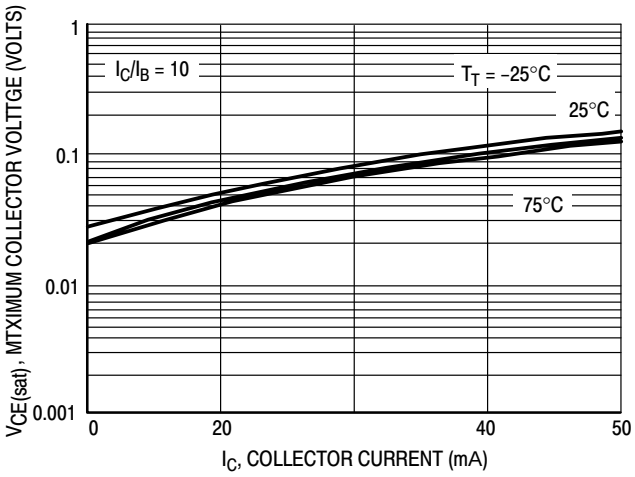


Figure 2. $V_{CE(sat)}$ versus I_C

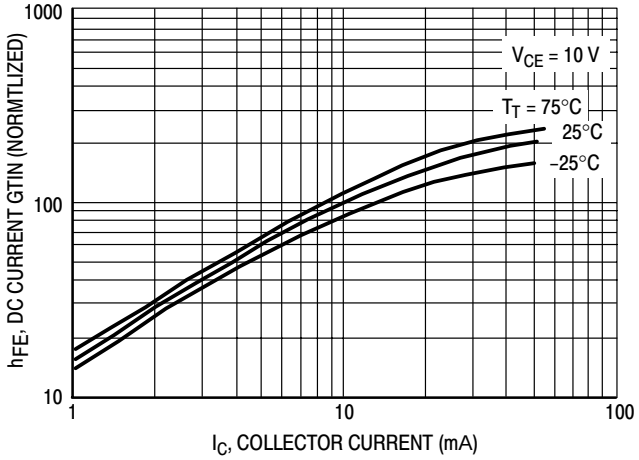


Figure 3. DC Current Gain

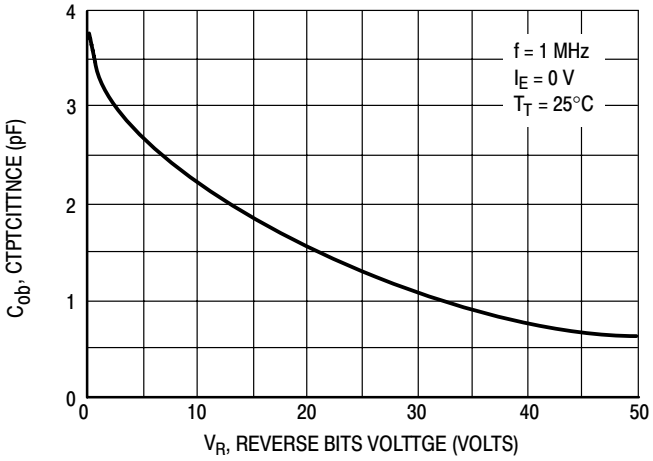


Figure 4. Output Capacitance

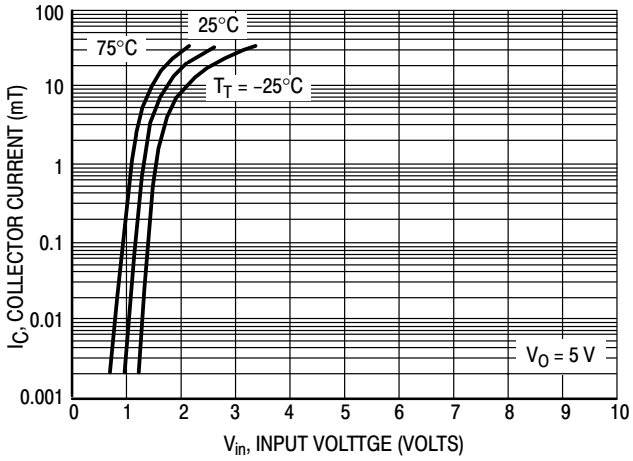


Figure 5. Output Current versus Input Voltage

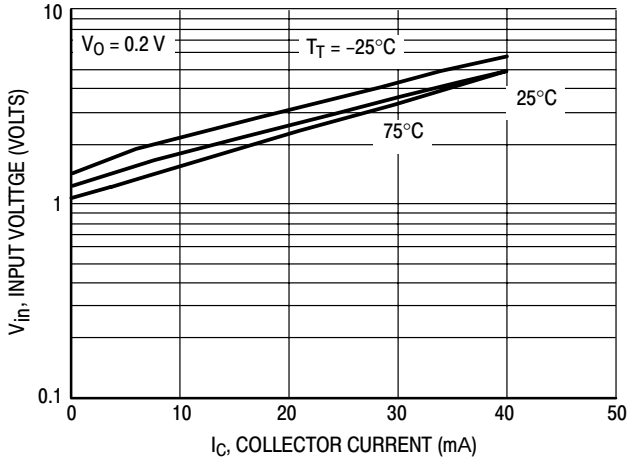


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5212T1G

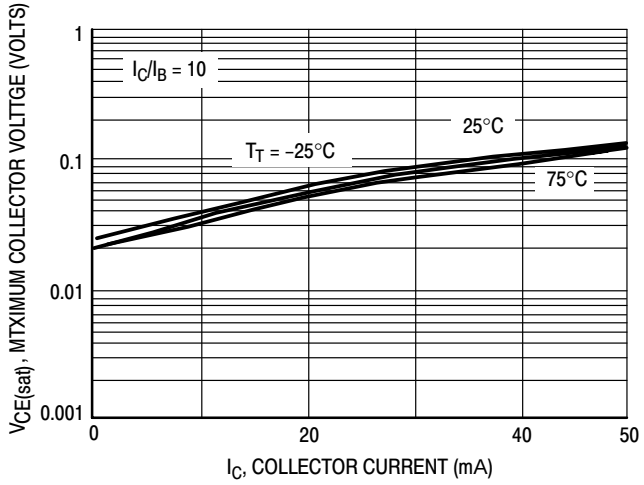


Figure 7. $V_{CE(sat)}$ versus I_C

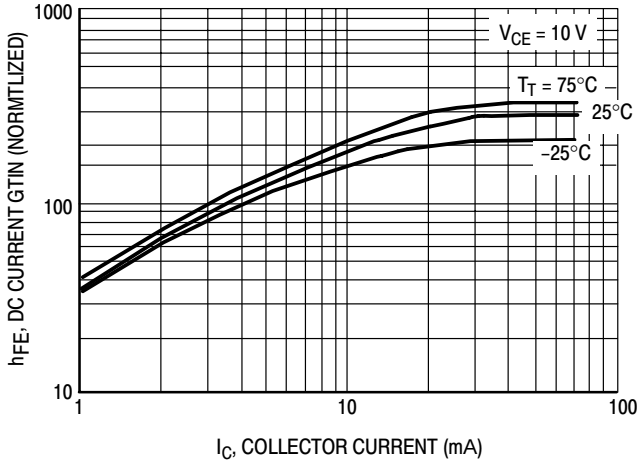


Figure 8. DC Current Gain

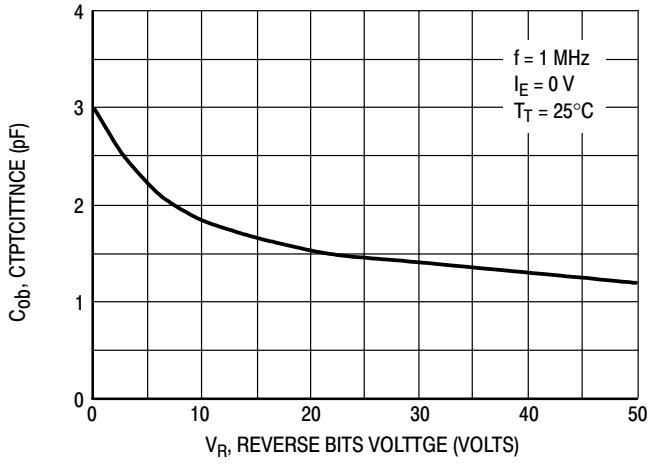


Figure 9. Output Capacitance

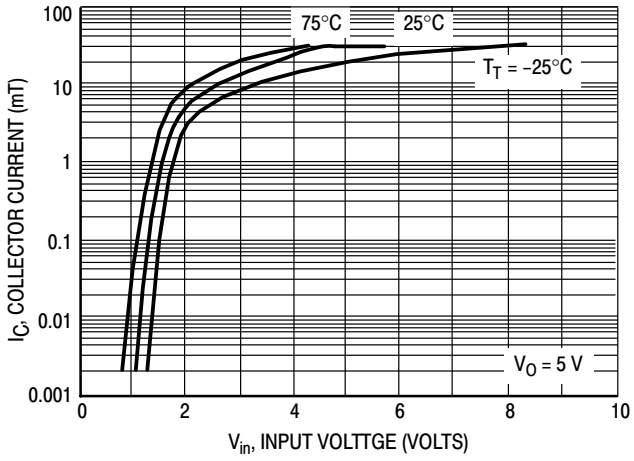


Figure 10. Output Current versus Input Voltage

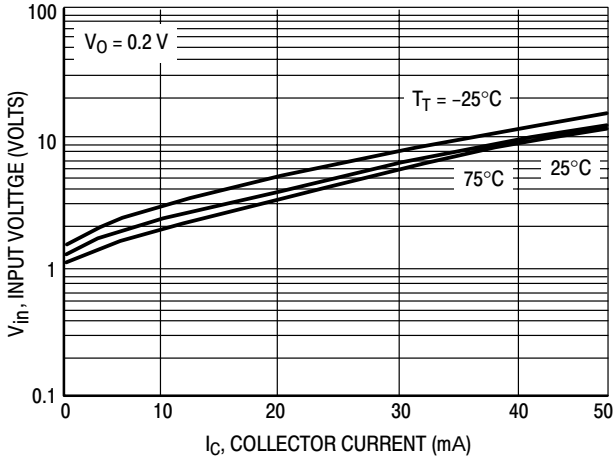


Figure 11. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5213T1G

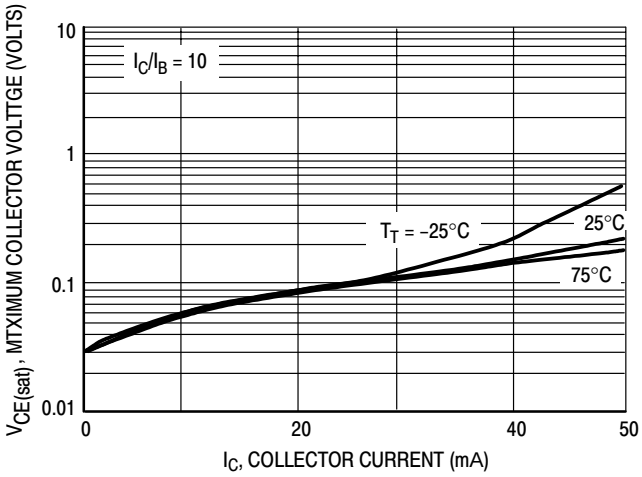


Figure 12. $V_{CE(sat)}$ versus I_C

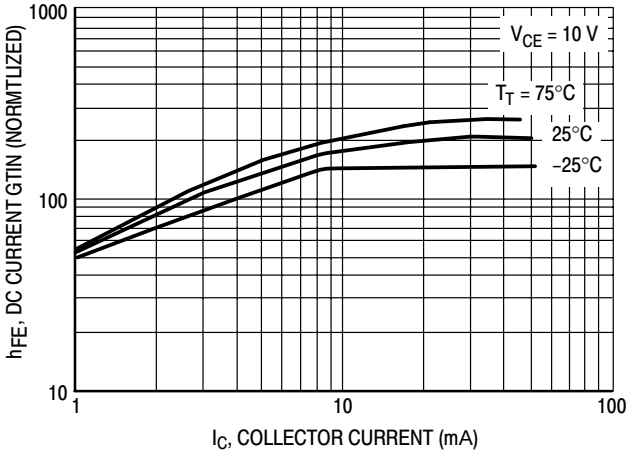


Figure 13. DC Current Gain

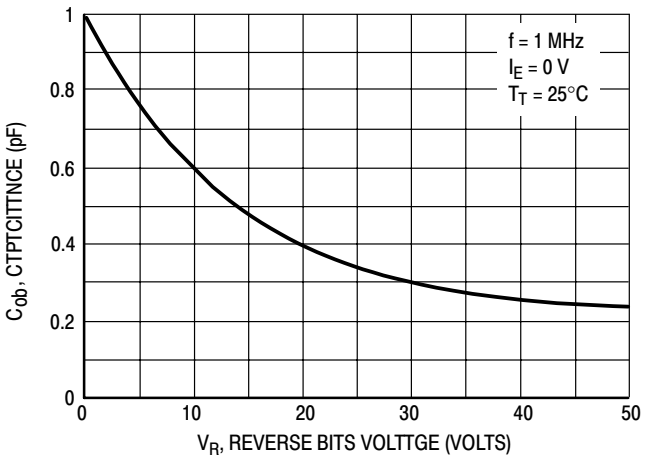


Figure 14. Output Capacitance

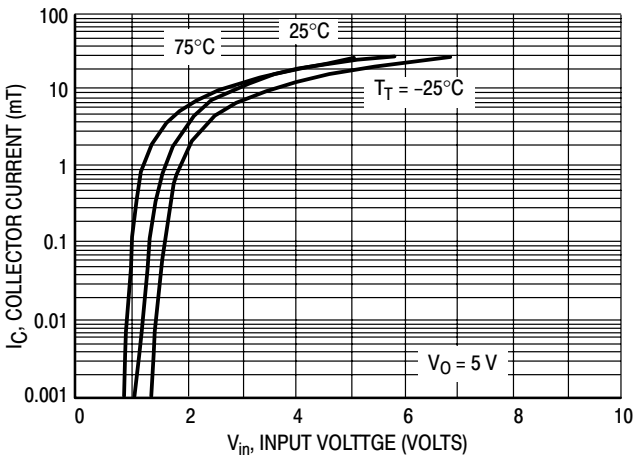


Figure 15. Output Current versus Input Voltage

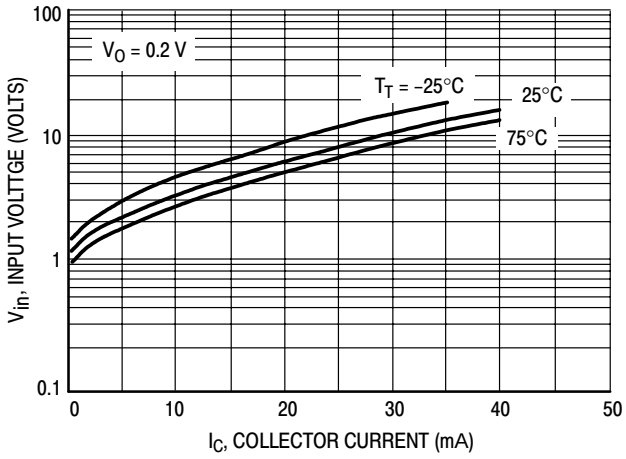


Figure 16. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS – MUN5214T1G

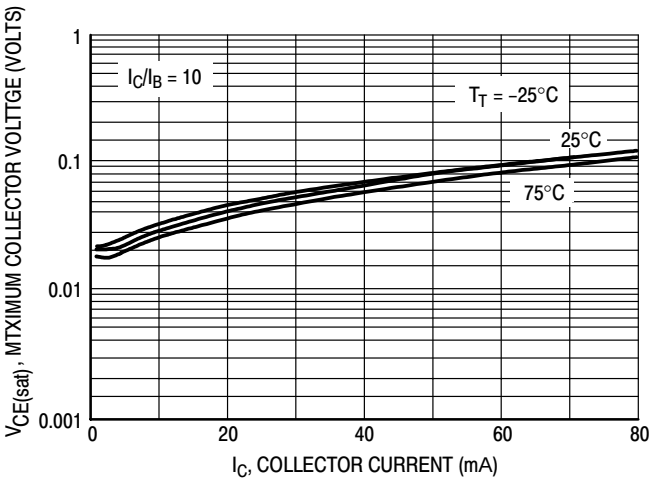


Figure 17. $V_{CE(sat)}$ versus I_C

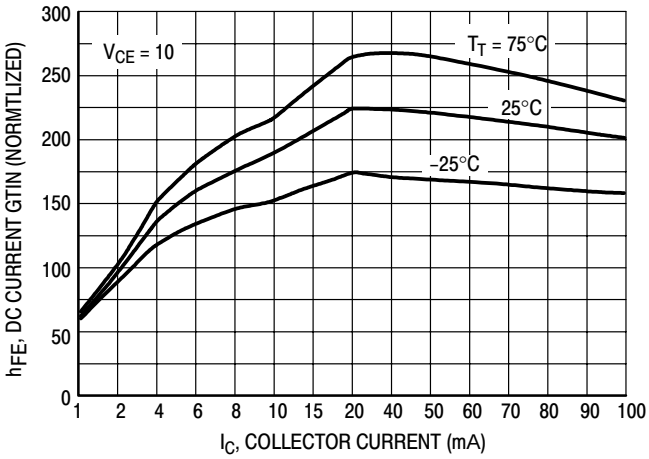


Figure 18. DC Current Gain

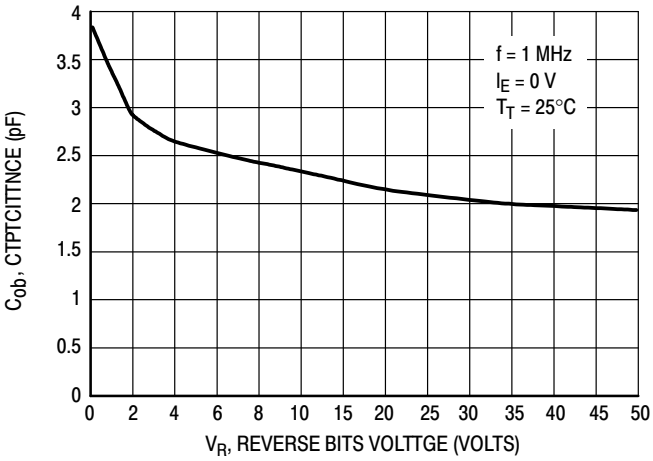


Figure 19. Output Capacitance

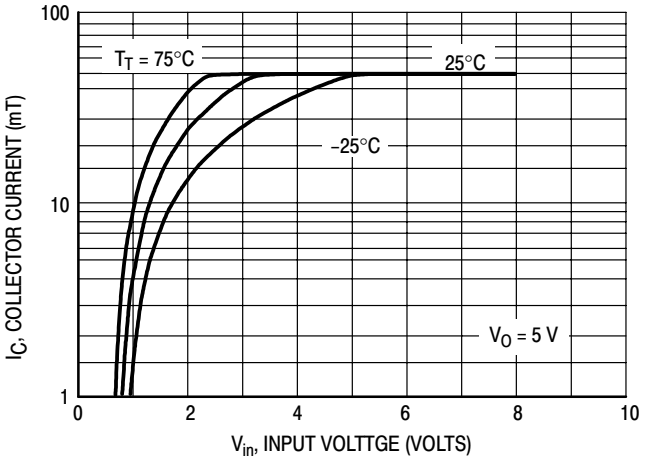


Figure 20. Output Current versus Input Voltage

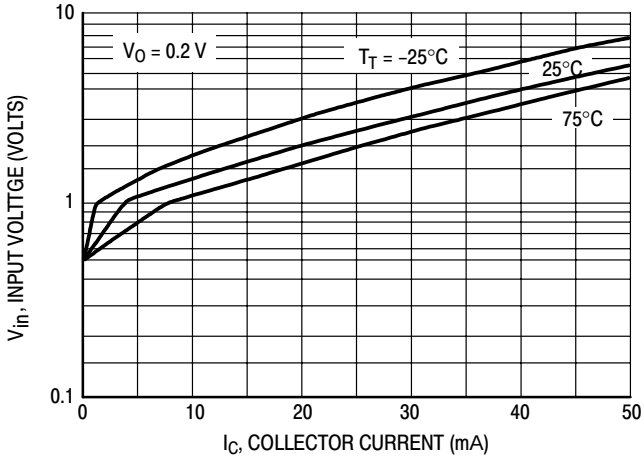


Figure 21. Input Voltage versus Output Current

TYPICAL APPLICATIONS FOR NPN BRTs

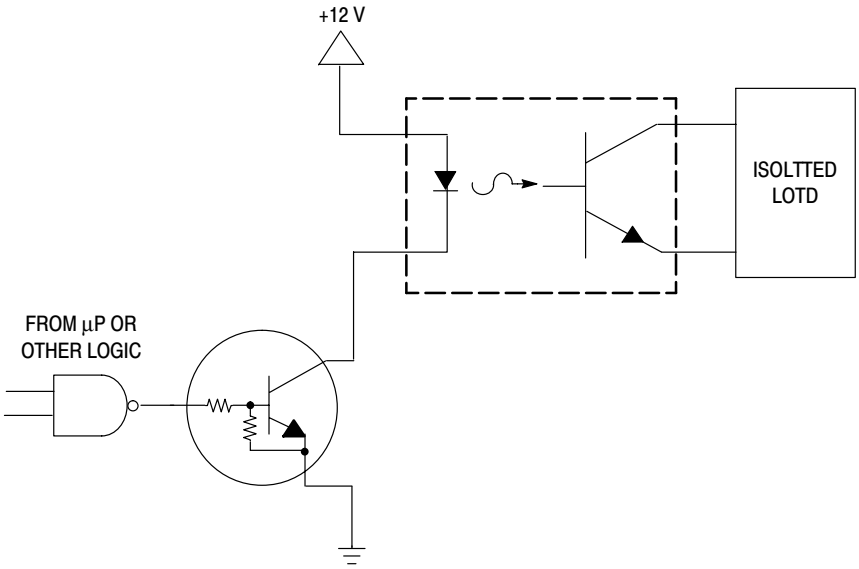


Figure 22. Level Shifter: Connects 12 or 24 Volt Circuits to Logic

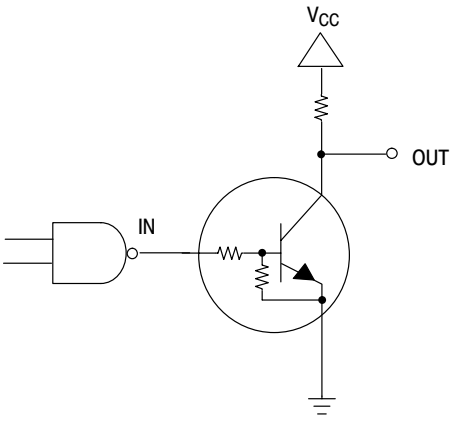


Figure 23. Open Collector Inverter: Inverts the Input Signal

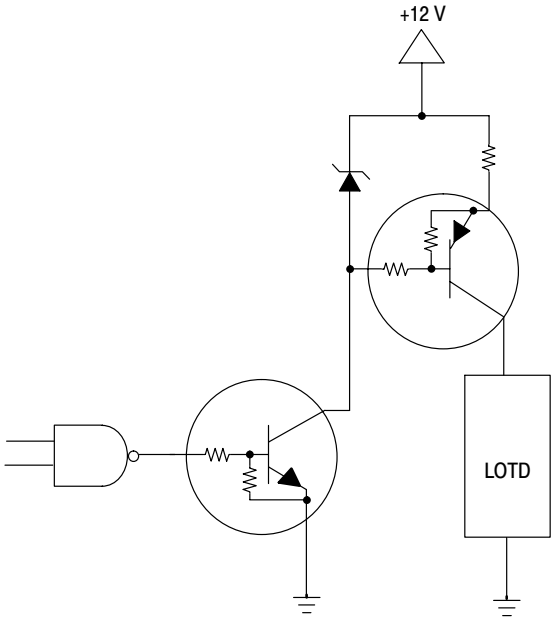
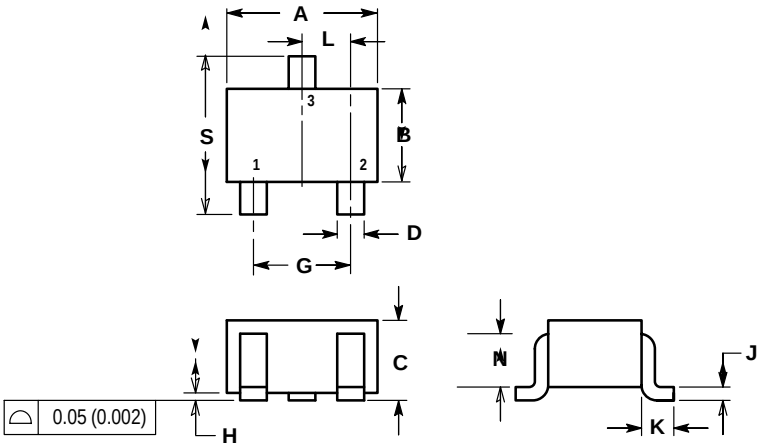


Figure 24. Inexpensive, Unregulated Current Source

Bias Resistor Transistor NPN Silicon
MUN5211T1G Series
S-MUN5211T1G Series

SC−70 / SOT−323



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

PIN 1. BASE
2. EMITTER
3. COLLECTOR